

# Filip Guemann

## List of Publications by Year in descending order

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Version: 2024-02-01

35  
papers

203  
citations

1039406

9  
h-index

1125271

13  
g-index

36  
all docs

36  
docs citations

36  
times ranked

282  
citing authors

#	ARTICLE	IF	CITATIONS
1	InN crystal habit, structural, electrical, and optical properties affected by sapphire substrate nitridation in N-polar InN/InAlN heterostructures. <i>Semiconductor Science and Technology</i> , 2021, 36, 075025.	1.0	0
2	Doping efficiency and electron transport in Al-doped ZnO films grown by atomic layer deposition. <i>Journal of Applied Physics</i> , 2021, 130, 035106.	1.1	5
3	Extraction and characterization of polysaccharide films prepared from <i>Furcellaria lumbricalis</i> and <i>Gigartina skottsbergii</i> seaweeds. <i>Cellulose</i> , 2021, 28, 9567-9588.	2.4	10
4	Scanning thermal microscopy for accurate nanoscale device thermography. <i>Nano Today</i> , 2021, 39, 101206.	6.2	15
5	Invited: Polarization engineering in GaN-based normally-off transistors. , 2021, , .		0
6	A systematic study of MOCVD reactor conditions and Ga memory effect on properties of thick InAl(Ga)N layers: a complete depth-resolved investigation. <i>CrystEngComm</i> , 2020, 22, 130-141.	1.3	2
7	Growth and Properties of N-polar InN/InAlN Heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 2000197.	0.8	4
8	Investigation of interfaces and threshold voltage instabilities in normally-off MOS-gated InGaN/AlGaIn/GaN HEMTs. <i>Applied Surface Science</i> , 2020, 528, 146824.	3.1	3
9	Semi-insulating GaN for vertical structures: role of substrate selection and growth pressure. <i>Materials Science in Semiconductor Processing</i> , 2020, 118, 105203.	1.9	7
10	Growth of $\text{In}^{\pm}$ - and $\text{In}^2\text{-Ga}_{2\text{O}_3}$ epitaxial layers on sapphire substrates using liquid-injection MOCVD. <i>Semiconductor Science and Technology</i> , 2020, 35, 115002.	1.0	13
11	Morphology, Crystalline Quality, and Optical Properties of MOCVD-grown InN/InAlN Heterostructures. , 2020, , .		1
12	High Efficiency AlN/GaN HEMTs for Q-Band Applications with an Improved Thermal Dissipation. <i>Selected Topics in Electronics and Systems</i> , 2020, , 51-62.	0.2	1
13	Effect of annealing temperature on diamond/Si interfacial structure. , 2019, , .		0
14	Evidence of relationship between strain and In-incorporation: Growth of N-polar In-rich InAlN buffer layer by OMCVD. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	10
15	Annealing effect of surface-activated bonded diamond/Si interface. <i>Diamond and Related Materials</i> , 2019, 93, 187-192.	1.8	30
16	High Efficiency AlN/GaN HEMTs for Q-Band Applications with an Improved Thermal Dissipation. <i>International Journal of High Speed Electronics and Systems</i> , 2019, 28, 1940003.	0.3	3
17	Thermal analysis of semiconductor devices and materials - Why should I not trust a thermal simulation ? . , 2019, , .		6
18	Impact of oxide/barrier charge on threshold voltage instabilities in AlGaIn/GaN metal-oxide-semiconductor heterostructures. <i>Materials Science in Semiconductor Processing</i> , 2019, 91, 356-361.	1.9	4

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19	Creation of Two-Dimensional Electron Gas and Role of Surface Donors in III-N Metal-Oxide-Semiconductor High-Electron Mobility Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1800090.	0.8	5
20	Technology and application of in-situ AlO <sub>x</sub> layers on III-V semiconductors. <i>Applied Surface Science</i> , 2018, 461, 33-38.	3.1	1
21	Properties of InGaAs/GaAs metal-oxide-semiconductor heterostructure field-effect transistors modified by surface treatment. <i>Applied Surface Science</i> , 2017, 395, 140-144.	3.1	10
22	Optimization of UV-assisted wet oxidation of GaAs. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017, 35, .	0.6	0
23	Low-temperature atomic layer deposition-grown Al <sub>2</sub> O <sub>3</sub> gate dielectric for GaN/AlGaIn/GaN MOS HEMTs: Impact of deposition conditions on interface state density. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017, 35, .	0.6	21
24	Investigation of $\tilde{\sigma}$ -surface donors <sup>TM</sup> in Al <sub>2</sub> O <sub>3</sub> /AlGaIn/GaN metal-oxide-semiconductor heterostructures: Correlation of electrical, structural, and chemical properties. <i>Applied Surface Science</i> , 2017, 426, 656-661.	3.1	27
25	Threshold voltage instabilities in AlGaIn/GaN MOS-HEMTs with ALD-grown Al <sub>2</sub> O <sub>3</sub> gate dielectrics: Relation to distribution of oxide/semiconductor interface state density. , 2016, , .		0
26	Effect of HCl pretreatment on the oxide/semiconductor interface state density in AlGaIn/GaN MOS-HEMT structures with MOCVD grown Al <sub>2</sub> O <sub>3</sub> gate dielectric. , 2016, , .		0
27	DC and pulsed IV characterisation of AlGaIn/GaN MOS-HEMT structures with Al <sub>2</sub> O <sub>3</sub> gate dielectric prepared by various techniques. , 2016, , .		0
28	III-As heterostructure field-effect transistors with recessed ex-situ gate oxide by O <sub>2</sub> plasma-oxidized GaAs cap. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, 01A111.	0.6	3
29	Vortex Dynamics in Ferromagnetic Nanoelements Observed by Micro-Hall Probes. <i>Acta Physica Polonica A</i> , 2014, 126, 390-391.	0.2	0
30	InGaAs/GaAs metal-oxide-semiconductor heterostructure field-effect transistors with oxygen-plasma oxide and Al <sub>2</sub> O <sub>3</sub> double-layer insulator. <i>Applied Physics Letters</i> , 2014, 105, 183504.	1.5	10
31	Scaling of the physical properties in Ba(Fe,Ni) <sub>2</sub> As <sub>2</sub> single crystals: Evidence for quantum fluctuations. <i>Physical Review B</i> , 2012, 85, .	1.1	8
32	Nucleation and annihilation of magnetic vortices in Pacman-like nanodots observed by micro-Hall probes. , 2012, , .		0
33	Properties of Al <sub>2</sub> O <sub>3</sub> thin films grown by atomic layer deposition. , 2012, , .		3
34	Distribution of fixed oxide charge in MOS structures with ALD grown Al <sub>2</sub> O <sub>3</sub> studied by capacitance measurements. , 2012, , .		1
35	The influence of an AlO <sub>x</sub> film in-situ deposited on the GaAs-based HFETs properties. , 2012, , .		0